

# **2023 35th International Symposium on Power Semiconductor Devices and ICs (ISPSD 2023)**

**Hong Kong  
28 May – 1 June 2023**



**IEEE Catalog Number: CFP23ISP-POD  
ISBN: 979-8-3503-9683-6**

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|-------------------------|-------------------|
| IEEE Catalog Number:    | CFP23ISP-POD      |
| ISBN (Print-On-Demand): | 979-8-3503-9683-6 |
| ISBN (Online):          | 979-8-3503-9682-9 |
| ISSN:                   | 1063-6854         |

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# TABLE OF CONTENTS

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**Monday, May 29, 2023**

**9:10 – 9:50**

**Plenary Talk Day 1**

**Chairs:** Kevin J. Chen, *The Hong Kong University of Science and Technology*  
Ichiro Omura, *Kyushu Institute of Technology*

**9:10**

**The Future of XPU Power Delivery for Artificial Intelligence**

Jinghai Zhou  
*Monolithic Power Systems*

**9:50**

**Unleashing the Potential of  $\alpha$ -Ga<sub>2</sub>O<sub>3</sub> Gallium Oxide Power Device**

Kengo Takeuchi  
*FloSfia Inc.*

**10:50 – 12:30**

**SiC-1: Novel Device Structures in SiC**

**Chairs:** Siddarth Sundaresan, *Navitas*  
Ulrike Grossner, *ETH*

**10:50**

**Proposal of Vertical-Channel Fin-SiC MOSFET Toward Future Device Scaling ..... 1**

Haruka Shimizu<sup>1</sup>, Takeru Suto<sup>1</sup>, Hiroshi Miki<sup>1</sup>, Yuki Mori<sup>1</sup>, Digh Hisamoto<sup>1</sup>, Akio Shima<sup>1</sup>, Koyo Kinoshita<sup>2</sup>,  
Tatsunori Murata<sup>2</sup>, Tetsuo Oda<sup>2</sup>  
<sup>1</sup>Hitachi, Ltd.; <sup>2</sup>Hitachi Power Semiconductor Device, Ltd.

**11:15**

**First Demonstration of 600 V 4H-SiC Lateral Bi-Directional Metal-Oxide-Semiconductor  
Field-Effect Transistor (LBiDMOS) ..... 5**

Seung Yup Jang, Sundar Babu Isukapati, Dongyoung Kim, Woongje Sung  
*State University of New York Polytechnic Institute*

**11:40**

**Gate Impedance Analysis of SiC Power MOSFETs with SiO<sub>2</sub> and High- $\kappa$  Dielectric ..... 9**

Salvatore Race<sup>1</sup>, Piyush Kumar<sup>1</sup>, Philipp Natzke<sup>1</sup>, Ivana Kovacevic-Badstuebner<sup>1</sup>, Marianne Etzelmüller Bathen<sup>1</sup>,  
Ulrike Grossner<sup>1</sup>, Gianpaolo Romano<sup>2</sup>, Yulieth Arango<sup>2</sup>, Sami Bolat<sup>2</sup>, Stephan Wirths<sup>2</sup>, Lars Knoll<sup>2</sup>, Andrei Mihaila<sup>2</sup>  
<sup>1</sup>APS Laboratory, ETH Zürich; <sup>2</sup>Hitachi Energy Semiconductors

**12:05**

**Demonstration of 3.5kV SiC Deep-Implanted Superjunction Didoes ..... 13**

Reza Ghandi<sup>1</sup>, Collin Hitchcock<sup>1</sup>, Stacey Kennerly<sup>1</sup>, Mohamed Torky<sup>2</sup>, T. Paul Chow<sup>2</sup>  
<sup>1</sup>GE Research Center; <sup>2</sup>Rensselaer Polytechnic Institute

**14:00 – 15:40**

**GaN-1: GaN Power Device Reliability**

**Chairs:** Shu Yang, *University of Science and Technology of China*  
Sameh Khalil, *Infineon Technologies*

**14:00**

**Impacts of n-GaN Doping Concentration on Gate Reliability of p-n Junction/AlGaIn/GaN HEMTs ..... 16**

Chengcai Wang, Haohao Chen, Zuoheng Jiang, Junting Chen, Mengyuan Hua  
*Southern University of Science and Technology*

**14:25**

**Gate Lifetime of P-Gate GaN HEMT in Inductive Power Switching ..... 20**

Bixuan Wang<sup>1</sup>, Ruizhe Zhang<sup>1</sup>, Hengyu Wang<sup>2</sup>, Quanbo He<sup>2</sup>, Qihao Song<sup>1</sup>, Qiang Li<sup>1</sup>, Florin Udrea<sup>2</sup>, Yuhao Zhang<sup>1</sup>  
<sup>1</sup>*Virginia Polytechnic Institute and State University*; <sup>2</sup>*University of Cambridge*

**14:50**

**Impact of Inadequate Mg Activation on Dynamic Threshold Voltage of Schottky-Type p-GaN Gate HEMTs ..... 24**

Jiahui Sun, Zheyang Zheng, Li Zhang, Yat Hon Ng, Ji Shu, Tao Chen, Kevin J. Chen  
*The Hong Kong University of Science and Technology*

**15:15**

**Surge Current Ruggedness in Vertical GaN-on-GaN PiN Diode: Role of Conductivity Modulation ..... 28**

Jiahong Du<sup>1</sup>, Shu Yang<sup>1,2</sup>, Guangwei Xu<sup>1</sup>, Shibing Long<sup>1</sup>  
<sup>1</sup>*University of Science and Technology of China*; <sup>2</sup>*Zhejiang University*

**16:00 – 17:15**

**LVT-1: Vertical Low Voltage Devices**

**Chairs:** Amit Paul, *ON Semiconductor*  
Tatsuya Nishiwaki, *Toshiba Electronic Devices & Storage Corporation*

**16:00**

**Strain Engineering in Modern Si Trench Power MOSFETs – A Performance Booster for Future Generations ..... 32**

Stefan Karner<sup>1,2</sup>, Oliver Blank<sup>1</sup>, Jozef Keckes<sup>2</sup>, Maximilian Rösch<sup>1</sup>, Seung Hwan Lee<sup>1</sup>, Sylvain Leomant<sup>1</sup>  
<sup>1</sup>*Infineon Technologies Austria AG*; <sup>2</sup>*University of Leoben*

**16:25**

**Investigation of  $BV_{dss}$  Instability in Trench Power MOSFET Through DLTS, Electrical Characterization and TCAD Simulations ..... 36**

Marina Ruggeri<sup>1,2</sup>, Patrick Calenzo<sup>1</sup>, Frédéric Morancho<sup>2</sup>, Lia Masoero<sup>1</sup>, Rosalia Germana<sup>1</sup>, Alessandro Nodari<sup>1</sup>, Richard Monflier<sup>2</sup>  
<sup>1</sup>*STMicroelectronics*; <sup>2</sup>*LAAS-CNRS*

**16:50**

**High Performance Dual Field Plate Trench MOSFETs for Middle-Voltage Applications ..... 40**

Shuhei Tokuyama, Hiroaki Kato, Tsuyoshi Kachi, Katsura Miyashita, Kenya Kobayashi  
*Toshiba Electronic Devices & Storage Corporation*

## Tuesday, May 30, 2023

8:45 – 10:05

### Plenary Talk Day 2

**Chairs:** Tom Tsai, *TSMC*  
Nando Kaminski, *University of Bremen*

8:45

### GaN Devices for Power System

Taikang Shing  
*Ancora Semi, Inc.*

9:25

### Evolution of Automotive Power Modules

Matthias Hammerl  
*Vitesco Technologies GmbH*

10:25 – 12:30

### PK-1: Power Module Design & Development

**Chairs:** Ichiro Omura, *Kyushu Institute of Technology*  
Antonio Pio Catalano, *University of Naples*

10:25

### A SiC 3D Power IC Directly Integrating a Power MOSFET with its CMOS Gate Driver Using Flip Chip Bonding ..... 44

Atsushi Yao, Mitsuo Okamoto, Shinji Sato, Daiki Yamaguchi, Hiroshi Sato  
*National Institute of Advanced Industrial Science and Technology*

10:50

### Application-Oriented Characterization of Thermally Optimized, Asymmetrical Single Chip Packages for 100 V GaN HEMTs ..... 48

Dominik Koch<sup>1</sup>, Vladimir Polezhaev<sup>2</sup>, Ankit Bushan Sharma<sup>2</sup>, Kevin Muñoz Barón<sup>1</sup>, Till Huesgen<sup>2</sup>, Ingmar Kallfass<sup>1</sup>  
<sup>1</sup>Universität Stuttgart; <sup>2</sup>University of Applied Sciences Kempten

11:15

### SiC MOSFET Bi-Directional Switch IMS Module Design ..... 52

Yonghwa Lee<sup>1</sup>, Alberto Castellazzi<sup>1</sup>, Sébastien Avilès<sup>2</sup>, Cyrille Duchesne<sup>2</sup>, Philippe Lasserre<sup>2</sup>  
<sup>1</sup>Kyoto University of Advanced Science; <sup>2</sup>Deep Concept

11:40

### Package Design Consideration for Suppressing Radiated EMI Noise in Semi-Bridgeless PFC Converters ..... 56

Satoshi Yoshida<sup>1</sup>, Takenori Yasuzumi<sup>1</sup>, Tsuguhiro Tanaka<sup>2</sup>, Yasuyuki Fujiwara<sup>2</sup>  
<sup>1</sup>Toshiba Corporation; <sup>2</sup>Toshiba Electronic Devices & Storage Corporation

12:05

### Power Cycling of Sintered SiC Power MOSFET Baseplate-Less Modules with Aluminum Oxide and Silicon Nitride Substrates ..... 60

Ivana Kovacevic-Badstuebner<sup>1</sup>, Elena Mengotti<sup>2</sup>, Philipp Natzke<sup>1</sup>, Salvatore Race<sup>1</sup>, Enea Bianda<sup>2</sup>, Joni Jormanainen<sup>3</sup>, Ulrike Grossner<sup>2</sup>  
<sup>1</sup>APS Laboratory, ETH Zürich; <sup>2</sup>ABB Switzerland Ltd.; <sup>3</sup>ABB Drives Oy

**14:00 – 16:05**

**ICD-1: ICs for Drivers & Protection Circuits**

**Chairs:** Makoto Takamiya, *The University of Tokyo*  
John Pigott, *NXP Semiconductors*

**14:00**

**p-GaN HEMT Hard Switching Fault Type Short-Circuit Detection Based on the Gate Schottky-Barrier Leakage Current and Using a Dual-Channel Segmented CMOS Buffer Gate-Driver ..... 64**

Yazan Barazi, Frédéric Richardeau, Sébastien Vinnac, Nicolas Rouger  
*Université de Toulouse*

**14:25**

**CMOS Gate Driver with Integrated Ultra-Accurate and Fast Gate Charge Sensor for Robust and Ultra-Fast Short Circuit Detection of SiC Power Modules ..... 68**

Anas El Boubkari<sup>1,2</sup>, Nicolas Rouger<sup>2</sup>, Frédéric Richardeau<sup>2</sup>, Marc Cousineau<sup>2</sup>, Thierry Sicard<sup>1</sup>,  
Pierre Calmes<sup>1</sup>, Matthew Bacchi<sup>1</sup>  
<sup>1</sup>*NXP Semiconductors*; <sup>2</sup>*Université de Toulouse*

**14:50**

**Novel Multifunctional Transient Voltage Suppressor Technology for Modular EOS/ESD Protection Circuit Designs ..... 72**

Zhao Qi, Ming Qiao, Jingqi Wei, Yonggang Shi, Hongquan Chen, Zhaoji Li, Bo Zhang  
*University of Electronic Science and Technology of China*

**15:15**

**Gate Driver IC with Fully Integrated Overcurrent Protection Function by Measuring Gate-to-Emitter Voltage During IGBT Conduction ..... 76**

Haifeng Zhang<sup>1</sup>, Dibo Zhang<sup>1</sup>, Hiromu Yamasaki<sup>1</sup>, Katsuhiko Hata<sup>1</sup>, Keiji Wada<sup>2</sup>, Kan Akatsu<sup>3</sup>,  
Ichiro Omura<sup>4</sup>, Makoto Takamiya<sup>1</sup>  
<sup>1</sup>*The University of Tokyo*; <sup>2</sup>*Tokyo Metropolitan University*; <sup>3</sup>*Yokohama National University*;  
<sup>4</sup>*Kyushu Institute of Technology*

**15:40**

**Monolithic FET-Controlled GaN Driver with Pre-Boosting and Robust Dead Time Control for DToF LiDAR Application ..... 80**

Chun-Wang Zhuang, Xin Ming, Zi-Kai Ye, Yao Qin, Zhi-Yi Lin, William Li, Hui Yan, Bo Zhang  
*University of Electronic Science and Technology of China*

**16:20 – 17:50**

**Poster-1: GaN**

**Chair:** Oliver Hilt, *Ferdinand Braun Institut*

**Poster Area**

**Failure Process of GaN-HEMTs by Repetitive Overvoltage Stress ..... 84**

Wataru Saito, Shin-Ichi Nishizawa  
*Kyushu University*

**Vertical GaN Schottky Barrier Diode with Record High FOM (1.23GW/cm<sup>2</sup>) Fully Grown by Hydride Vapor Phase Epitaxy ..... 88**

Ping Zou<sup>1</sup>, Haofan Wang<sup>1</sup>, Junye Wu<sup>1</sup>, Zeliang Liao<sup>1</sup>, Shuangwu Huang<sup>1</sup>, Ze Zhong<sup>1</sup>, Xiaobo Li<sup>1</sup>, Feng Qiu<sup>2</sup>,  
Wenrong Zhuang<sup>3</sup>, Longkou Chen<sup>4</sup>, Xinke Liu<sup>1</sup>  
<sup>1</sup>*Shenzhen University*; <sup>2</sup>*Gensol (Shenzhen) Tech. Innovation Center Co., Ltd*; <sup>3</sup>*Dongguan Sino Nitride Semiconductor Co., Ltd*; <sup>4</sup>*Shenzhen Baseus Technology Co., Ltd*

|                                                                                                                                                                                                                                                                                                                                                                            |            |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------|
| <b>Enhanced Gate Breakdown and Electroluminescence in p-GaN Gate HEMTs Under Pulsed Switching Conditions .....</b>                                                                                                                                                                                                                                                         | <b>91</b>  |
| Huan Wang <sup>1</sup> , Yulian Yin <sup>1</sup> , Fengwei Ji <sup>1</sup> , Jiahong Du <sup>2</sup> , Haoran Li <sup>1</sup> , Changhui Zhao <sup>1</sup> , Baikui Li <sup>3</sup> , Cungang Hu <sup>1</sup> , Wenping Cao <sup>1</sup> , Xi Tang <sup>1</sup> , Shu Yang <sup>2</sup>                                                                                    |            |
| <i><sup>1</sup>Anhui University; <sup>2</sup>University of Science and Technology of China; <sup>3</sup>Shenzhen University</i>                                                                                                                                                                                                                                            |            |
| <b>A Systematic Characterization Method for Time-Resolved Stability and Reliability Issues on Lateral GaN Power Devices .....</b>                                                                                                                                                                                                                                          | <b>95</b>  |
| Yifei Huang <sup>1,2</sup> , Qimeng Jiang <sup>1</sup> , Sen Huang <sup>1,2</sup> , Xinyu Liu <sup>1,2</sup>                                                                                                                                                                                                                                                               |            |
| <i><sup>1</sup>Institute of Microelectronics of the Chinese Academy of Sciences; <sup>2</sup>University of Chinese Academy of Sciences</i>                                                                                                                                                                                                                                 |            |
| <b>Demonstration of the Hydrogen Passivated GaN HEMTs IC Platform .....</b>                                                                                                                                                                                                                                                                                                | <b>99</b>  |
| Fan Li <sup>1,3</sup> , Ang Li <sup>1,3</sup> , Yubo Wang <sup>1</sup> , Yuhao Zhu <sup>1,3</sup> , Chengruiyuan Yu <sup>1</sup> , Chengmurong Ding <sup>1</sup> , Shiqiang Wu <sup>1</sup> , Wen Liu <sup>1</sup> , Guohao Yu <sup>2,4</sup> , Xiaotian Gao <sup>4</sup> , Zheming Wang <sup>0</sup> , Baoshun Zhang <sup>0</sup>                                         |            |
| <i><sup>1</sup>Xi'an Jiaotong-Liverpool University; <sup>2</sup>University of Science and Technology of China; <sup>3</sup>University of Liverpool; <sup>4</sup>Suzhou Institute of Nano-Tech and Nano-Bionics, CAS</i>                                                                                                                                                    |            |
| <b>700 V/2.5 a Normally-Off Ultrathin-Barrier AlGaN(&lt;6nm)/GaN MIS-HEMTs with Improved Gate Overdrive Window and PBTI .....</b>                                                                                                                                                                                                                                          | <b>103</b> |
| Tiantian Luan <sup>1,2</sup> , Sen Huang <sup>1,2</sup> , Yixu Yao <sup>1,2</sup> , Qimeng Jiang <sup>1,2</sup> , Yuhao Wang <sup>1,2</sup> , Yifei Huang <sup>1,2</sup> , Chao Feng <sup>1,2</sup> , Xinhua Wang <sup>1,2</sup> , Xinyu Liu <sup>1,2</sup> , Ronghua Wang <sup>3</sup> , Yongshuo Ren <sup>3</sup> , Wanxi Cheng <sup>3</sup> , Huinan Liang <sup>3</sup> |            |
| <i><sup>1</sup>Institute of Microelectronics, Chinese Academy of Sciences; <sup>2</sup>University of Chinese Academy of Sciences; <sup>3</sup>Runxin Microelectronics Corporation</i>                                                                                                                                                                                      |            |
| <b>Switching Performance of GaN p-FET-Bridge (PFB-) HEMTs Studied with Mixed-Mode TCAD Simulation .....</b>                                                                                                                                                                                                                                                                | <b>107</b> |
| Junting Chen <sup>1,2</sup> , Tao Chen <sup>2</sup> , Zuoheng Jiang <sup>1</sup> , Chengcai Wang <sup>1</sup> , Zheyang Zheng <sup>2</sup> , Jin Wei <sup>3</sup> , Kevin J. Chen <sup>2</sup> , Mengyuan Hua <sup>1</sup>                                                                                                                                                 |            |
| <i><sup>1</sup>Southern University of Science and Technology; <sup>2</sup>The Hong Kong University of Science and Technology; <sup>3</sup>Peking University</i>                                                                                                                                                                                                            |            |
| <b>Exploitation of Hole Injection and Spreading for Dynamic Enhancement in p-GaN Gate HEMT Under Room/High Temperatures .....</b>                                                                                                                                                                                                                                          | <b>111</b> |
| Junjie Yang, Yanlin Wu, Muqin Nuo, Zhenghao Chen, Xuelin Yang, Bo Shen, Maojun Wang, Jin Wei                                                                                                                                                                                                                                                                               |            |
| <i>Peking University</i>                                                                                                                                                                                                                                                                                                                                                   |            |
| <b>Threshold Voltage Instability of Schottky-Type p-GaN Gate HEMT Down to Cryogenic Temperatures .....</b>                                                                                                                                                                                                                                                                 | <b>115</b> |
| Xinyu Wang, Zuoheng Jiang, Junting Chen, Junlei Zhao, Han Wang, Chengcai Wang, Haohao Chen, Jun Ma, Xiaolong Chen, Mengyuan Hua                                                                                                                                                                                                                                            |            |
| <i>Southern University of Science and Technology</i>                                                                                                                                                                                                                                                                                                                       |            |
| <b>Total-Ionizing-Dose Radiation Induced Gate Damage in High Voltage p-GaN Gate HEMTs .....</b>                                                                                                                                                                                                                                                                            | <b>119</b> |
| Zhao Wang, Xin Zhou, Zhonghua Wu, Chen Chen, Qi Zhou, Ming Qiao, Zhaoji Li, Bo Zhang                                                                                                                                                                                                                                                                                       |            |
| <i>University of Electronic Science and Technology of China</i>                                                                                                                                                                                                                                                                                                            |            |
| <b>Comprehensive MVSG Compact Model for Power GaN Devices .....</b>                                                                                                                                                                                                                                                                                                        | <b>123</b> |
| Ryan Fang <sup>1</sup> , Yijing Feng <sup>1</sup> , Jessica Chong <sup>1</sup> , Kaiman Chan <sup>2</sup> , Ujwal Radhakrishna <sup>1,2</sup> , Lan Wei <sup>1</sup>                                                                                                                                                                                                       |            |
| <i><sup>1</sup>University of Waterloo; <sup>2</sup>Texas Instruments</i>                                                                                                                                                                                                                                                                                                   |            |
| <b>Method to Study Dynamic Depletion Behaviors in High-Voltage (BV = 1.4 kV) p-GaN Gate HEMT on Sapphire Substrate .....</b>                                                                                                                                                                                                                                               | <b>127</b> |
| Jiawei Cui <sup>1</sup> , Yanlin Wu <sup>1</sup> , Junjie Yang <sup>1</sup> , Jingjing Yu <sup>1</sup> , Teng Li <sup>1,2</sup> , Xuelin Yang <sup>3</sup> , Bo Shen <sup>3</sup> , Maojun Wang <sup>1</sup> , Jin Wei <sup>1</sup>                                                                                                                                        |            |
| <i><sup>1</sup>Peking University; <sup>2</sup>Beijing University of Technology</i>                                                                                                                                                                                                                                                                                         |            |

|                                                                                                                                                                                                                                                                                                                                                                                                                                                               |            |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------|
| <b>Suppressing the Reverse Recovery of Si Super-Junction MOSFET with a Low-Voltage GaN HEMT in a Cascode Configuration .....</b>                                                                                                                                                                                                                                                                                                                              | <b>131</b> |
| Ji Shu, Jiahui Sun, Zheyang Zheng, Kevin J. Chen<br><i>The Hong Kong University of Science and Technology</i>                                                                                                                                                                                                                                                                                                                                                 |            |
| <b>Dynamic Gate Capacitance Model for Switching Transient Analysis in p-GaN Gate HEMTs .....</b>                                                                                                                                                                                                                                                                                                                                                              | <b>135</b> |
| Caifen Sun, Zixu Niu, Shu Yang<br><i>Zhejiang University</i>                                                                                                                                                                                                                                                                                                                                                                                                  |            |
| <b>Ultra-Fast Positive Gate Bias Stress (&lt;100ns) to Understand the Hole Injection in Power p-GaN HEMTs .....</b>                                                                                                                                                                                                                                                                                                                                           | <b>139</b> |
| Zhen-Hong Huang <sup>1</sup> , Wei-Syuan Lin <sup>1</sup> , Ting-Chun Lo <sup>1</sup> , Shun-Wei Tang <sup>1</sup> , Szu-Chia Chen <sup>1</sup> , Dirk Wellekens <sup>2</sup> , Matteo Borga <sup>2</sup> , Niels Posthuma <sup>2</sup> , Benoit Bakeroot <sup>2,3</sup> , Stefaan Decoutere <sup>2</sup> , Tian-Li Wu <sup>1</sup><br><sup>1</sup> National Yang Ming Chiao Tung University; <sup>2</sup> imec; <sup>3</sup> CMST, imec and Ghent University |            |
| <b>Rapid Inverse Design of GaN-on-GaN Diode with Guard Ring Termination for BV and (V<sub>F</sub>Q)<sup>-1</sup> Co-Optimization .....</b>                                                                                                                                                                                                                                                                                                                    | <b>143</b> |
| Nathan Yee <sup>1</sup> , Albert Lu <sup>1</sup> , Yifan Wang <sup>2</sup> , Matthew Porter <sup>2</sup> , Yuhao Zhang <sup>2</sup> , Hiu Yung Wong <sup>1</sup><br><sup>1</sup> San Jose State University; <sup>2</sup> Virginia Polytechnic Institute and State University                                                                                                                                                                                  |            |
| <b>16:20 – 17:50</b>                                                                                                                                                                                                                                                                                                                                                                                                                                          |            |
| <b>Poster-1: HV</b>                                                                                                                                                                                                                                                                                                                                                                                                                                           |            |
| <b>Chair:</b> Shigeto Honda, <i>Mitsubishi Electric Corporation</i>                                                                                                                                                                                                                                                                                                                                                                                           |            |
| <i>Poster Area</i>                                                                                                                                                                                                                                                                                                                                                                                                                                            |            |
| <b>A 15V Operated Shallow Trench IGBT(ST-IGBT) Fabricated by Low Temperature Process and Optimized for 12Inch Wafers .....</b>                                                                                                                                                                                                                                                                                                                                | <b>147</b> |
| Masahiro Tanaka <sup>1</sup> , Naoki Abe <sup>1</sup> , Akio Nakagawa <sup>2</sup><br><sup>1</sup> Nihon Synopsys G.K.; <sup>2</sup> Nakagawa Consulting Office, LLC.                                                                                                                                                                                                                                                                                         |            |
| <b>Design of 1200-V RC-IGBT for TOYOTA's 5th Generation HEV/PHEV Systems .....</b>                                                                                                                                                                                                                                                                                                                                                                            | <b>151</b> |
| Jun Okawara <sup>1</sup> , Masaru Senoo <sup>1</sup> , Tsuyoshi Nishiwaki <sup>2</sup> , Yusuke Yamashita <sup>3</sup> , Satoru Machida <sup>3</sup> , Yuma Kagata <sup>1</sup> , Masaki Konishi <sup>1</sup><br><sup>1</sup> DENSO Corporation; <sup>2</sup> MIRISE Technologies Corporation; <sup>3</sup> Toyota Central R&D Labs., Inc.                                                                                                                    |            |
| <b>Separate-Bottom P Layer CSTBT™ for Approaching Turn-Off Switching Loss Reduction Limit .....</b>                                                                                                                                                                                                                                                                                                                                                           | <b>155</b> |
| Kazuya Konishi, Tetsuya Nitta, Tomohiro Tamaki, Shinya Soneda<br><i>Mitsubishi Electric Corporation</i>                                                                                                                                                                                                                                                                                                                                                       |            |
| <b>Si IGBT and SiC MOSFET – Potentials and Limitations of Plasma Shaping versus Unipolar Switching in Medium Power Applications .....</b>                                                                                                                                                                                                                                                                                                                     | <b>159</b> |
| Roman Baburske, Frank Pfirsch, Jana Hänsel, Katja Waschneck<br><i>Infineon Technologies AG</i>                                                                                                                                                                                                                                                                                                                                                                |            |
| <b>On the Electron Extraction Mechanism in Punch-Through NPN Fast Recovery Diodes .....</b>                                                                                                                                                                                                                                                                                                                                                                   | <b>163</b> |
| Xin Peng, Yong Liu, Hao Feng, Linhua Huang, Johnny K.O. Sin<br><i>The Hong Kong University of Science and Technology</i>                                                                                                                                                                                                                                                                                                                                      |            |
| <b>A SEB Hardened Trench Gate DMOS with HfO<sub>2</sub> Gate Dielectric and Decelerating Electric Field Layer in Parasitic NPN Base .....</b>                                                                                                                                                                                                                                                                                                                 | <b>167</b> |
| Jian Fang, Yibo Lei, Zhou Fang, Lijuan Shi, Lingli Tang, Xihe Yang, Ling Yan, Bo Zhang<br><i>University of Electronic Science and Technology of China</i>                                                                                                                                                                                                                                                                                                     |            |



|                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                     |            |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------|
| <b>Optimization of Reverse Recovery Characteristics Based on Termination Structure for 700V Super-Junction VDMOS .....</b>                                                                                                                                                                                                                                                                                                                                                                                                                                          | <b>171</b> |
| Yibing Wang, Ming Qiao, Jue Li, Ruidi Wang, Bo Zhang<br><i>University of Electronic Science and Technology of China</i>                                                                                                                                                                                                                                                                                                                                                                                                                                             |            |
| <b>A Novel IGBT with Variable Conductance Path Realizing Both Low <math>V_{on}</math> and Turn-Off Loss .....</b>                                                                                                                                                                                                                                                                                                                                                                                                                                                   | <b>175</b> |
| Yuxiao Yang <sup>1</sup> , Wanjun Chen <sup>1</sup> , Xinqi Sun <sup>1</sup> , Xiaorui Xu <sup>1</sup> , Yun Xia <sup>1</sup> , Chao Liu <sup>1</sup> , Zhaoji Li <sup>1</sup> , Bo Zhang <sup>1</sup> , Meng Wei <sup>2</sup> , Ping Zhang <sup>2</sup> , Zhong Ren <sup>3</sup><br><sup>1</sup> <i>University of Electronic Science and Technology of China</i> ; <sup>2</sup> <i>Sichuan Aerospace Liaoyuan Science and Technology Co.,LTD</i> ; <sup>3</sup> <i>China Academy of Aerospace Science and Innovation</i>                                           |            |
| <b>Experimental Demonstration of Point-Injection Trench IGBT Concept .....</b>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                      | <b>179</b> |
| Elizabeth Buitrago <sup>1</sup> , Marina Antoniou <sup>2</sup> , Nick Schneider <sup>1</sup> , Enea Bianda <sup>3</sup> , Luca De-Michieli <sup>1</sup> , Chiara Corvasce <sup>1</sup> , Florin Udrea <sup>4</sup><br><sup>1</sup> <i>Hitachi Energy Semiconductors</i> ; <sup>2</sup> <i>University of Warwick</i> ; <sup>3</sup> <i>ABB Switzerland Ltd.</i> ; <sup>4</sup> <i>University of Cambridge</i>                                                                                                                                                        |            |
| <b>A Novel Junction Termination Technique with Excellent Cost-Performance and Extraordinary Anti-Charge-Deviation Ability .....</b>                                                                                                                                                                                                                                                                                                                                                                                                                                 | <b>183</b> |
| Junji Cheng <sup>1,3</sup> , Weisen Meng <sup>1</sup> , Bo Yi <sup>1</sup> , Haimeng Huang <sup>1</sup> , Keqiang Ma <sup>2</sup> , Xinkai Guo <sup>1</sup> , Hongqiang Yang <sup>1</sup> , Zhiming Wang <sup>1</sup> , Guoyi Zhang <sup>3</sup><br><sup>1</sup> <i>University of Electronic Science and Technology of China</i> ; <sup>2</sup> <i>Chengdu Semi-Future Technology Co., Ltd.</i> ; <sup>3</sup> <i>Peking University</i>                                                                                                                             |            |
| <b>16:20 – 17:50</b>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                |            |
| <b>Poster-1: ICD</b>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                |            |
| <b>Chairs:</b> Xin Ming, <i>University of Electronic Science and Technology of China</i>                                                                                                                                                                                                                                                                                                                                                                                                                                                                            |            |
| <i>Poster Area</i>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                  |            |
| <b>Application of a Smart Gate Driver to Detect Aging in SiC Power MOSFETs .....</b>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                | <b>187</b> |
| Mengqi Wang <sup>1</sup> , Jiupeng Zhang <sup>1</sup> , Wai Tung Ng <sup>1</sup> , Haruhiko Nishio <sup>2</sup> , Motomitsu Iwamoto <sup>2</sup> , Hitoshi Sumida <sup>2</sup><br><sup>1</sup> <i>University of Toronto</i> ; <sup>2</sup> <i>Fuji Electric Co., Ltd.</i>                                                                                                                                                                                                                                                                                           |            |
| <b>Compact GaN Power ICs with Power HEMT, Gate Driver, Temperature Sensor, Current Sense-FET and Amplifier .....</b>                                                                                                                                                                                                                                                                                                                                                                                                                                                | <b>191</b> |
| Michael Basler <sup>1</sup> , Richard Reiner <sup>1</sup> , Stefan Moench <sup>1</sup> , Patrick Waltereit <sup>1</sup> , Rüdiger Quay <sup>1</sup> , Jörg Haarer <sup>2</sup><br><sup>1</sup> <i>Fraunhofer Institute for Applied Solid State Physics IAF</i> ; <sup>2</sup> <i>Universität Stuttgart</i>                                                                                                                                                                                                                                                          |            |
| <b>A 600-V GaN Active Gate Driver with Level Shifter Common-Mode Noise Sensing for Built-In dV/dt Self-Adaptive Control .....</b>                                                                                                                                                                                                                                                                                                                                                                                                                                   | <b>195</b> |
| Tianqi Liu, Rui P. Martins, Yan Lu<br><i>University of Macau</i>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                    |            |
| <b>Protection of SiC MOSFET from Negative Gate Voltage Spikes with a Low-Voltage GaN HEMT .....</b>                                                                                                                                                                                                                                                                                                                                                                                                                                                                 | <b>199</b> |
| Ji Shu, Jiahui Sun, Zheyang Zheng, Kevin J. Chen<br><i>The Hong Kong University of Science and Technology</i>                                                                                                                                                                                                                                                                                                                                                                                                                                                       |            |
| <b>A High-Speed Level Shifter with <math>dV_s/dt</math> Noise Immunity Enhancement Structure for 200V Monolithic GaN Power IC .....</b>                                                                                                                                                                                                                                                                                                                                                                                                                             | <b>203</b> |
| Yifei Zheng <sup>1</sup> , Qing Yuan <sup>1</sup> , Deyuan Song <sup>1</sup> , Yutao Ying <sup>1</sup> , Jing Zhu <sup>3</sup> , Weifeng Sun <sup>1</sup> , Long Zhang <sup>1</sup> , Sheng Li <sup>1</sup> , Denggui Wang <sup>2</sup> , Jianjun Zhou <sup>2</sup> , Sen Zhang <sup>4</sup> , Nailong He <sup>4</sup><br><sup>1</sup> <i>Southeast University</i> ; <sup>2</sup> <i>Nanjing Electronic Devices Institute, Science and Technology</i> ; <sup>3</sup> <i>Wuxi Chipown Micro-electronics Ltd.</i> ; <sup>4</sup> <i>CSMC Technologies Corporation</i> |            |

**Wednesday, May 31, 2023**

**8:45 – 10:25**

**HV-1: High Voltage Power Devices**

**Chairs:** Noriyuki Iwamuro, *University of Tsukuba*  
Yi Tang, *StarPower Semiconductor*

**8:45**

**Single-Back and Double-Front Gate-Controlled IGBT for Achieving Low Turn-Off Loss ..... 207**

Yusuke Kobayashi<sup>1</sup>, Munetoshi Fukui<sup>2</sup>, Tomoko Matsudai<sup>3</sup>, Takuya Saraya<sup>2</sup>, Kazuo Itou<sup>2</sup>, Toshihiko Takakura<sup>2</sup>, Shinichi Suzuki<sup>2</sup>, Ryohei Gejo<sup>3</sup>, Tatsunori Sakano<sup>1</sup>, Takahiro Kato<sup>1</sup>, Tomoaki Inokuchi<sup>1</sup>, Kazuto Takao<sup>1</sup>, Toshiro Hiramoto<sup>2</sup>

<sup>1</sup>Toshiba Corporation; <sup>2</sup>The University of Tokyo; <sup>3</sup>Toshiba Electronic Devices & Storage Corporation

**9:10**

**Novel Diode Structure for Ultra-Low-Loss RC-IGBTs ..... 211**

Yusuke Yamashita<sup>1</sup>, Satoru Machida<sup>1</sup>, Jun Saito<sup>2</sup>, Masaru Senoo<sup>3</sup>

<sup>1</sup>Toyota Central R&D Labs., Inc.; <sup>2</sup>MIRISE Technologies Corporation; <sup>3</sup>DENSO Corporation

**9:35**

**Reduction of Junction Temperature with Local Lifetime Control and High Density Arranged Diode for 3rd Gen. 650V RC-IGBT ..... 215**

Kosuke Sakaguchi, Kazuya Konishi, Keisuke Eguchi, Shinya Soneda  
*Mitsubishi Electric Corporation*

**10:00**

**A New Generation 700 V BCD Technology that Integrates Quadruple-RESURF LDMOS with Best-in-Class Specific On-Resistance ..... 219**

Ming Qiao, Dican Hou, Yue Gao, Dingxiang Ma, Jiawei Wang, Bo Zhang  
*University of Electronic Science and Technology of China*

**10:45 – 12:25**

**GaN-2: Novel GaN Power Devices & Technologies 1**

**Chairs:** Roy K.-Y. Wong, *Innoscence*  
Oliver Hilt, *Ferdinand Braun Institut*

**10:45**

**Demonstration of Fundamental Characteristics for Power Switching Application in Planer Type E-Mode MOS-HEMT Using Normally Depleted AlGaIn GaN Epitaxial Layer on Si Substrate ..... 223**

T. Nanjo<sup>1</sup>, S. Yamamoto<sup>1</sup>, T. Imazawa<sup>1</sup>, A. Kiyoi<sup>1</sup>, T. Shinagawa<sup>1</sup>, T. Watahiki<sup>1</sup>, N. Miura<sup>1</sup>, M. Furuhashi<sup>1</sup>, K. Nishikawa<sup>1</sup>, T. Egawa<sup>2</sup>

<sup>1</sup>Mitsubishi Electric Corporation; <sup>2</sup>Nagoya Institute of Technology

**11:10**

**GaN-HEMT with a Back-Gated Segment for High Voltage Cascodes ..... 227**

Richard Reiner, Stefan Moench, Patrick Waltereit, Michael Basler, Stefan Müller, Michael Mikulla, Rüdiger Quay  
*Fraunhofer Institute for Applied Solid State Physics IAF*

**11:35**

**Conductivity Enhancement Induced by Confined Vicinal Hole Storage in Enhancement-Mode p-GaN Gate Double-Channel HEMTs ..... 231**

Hang Liao<sup>1</sup>, Zheyang Zheng<sup>1</sup>, Tao Chen<sup>1</sup>, Li Zhang<sup>1</sup>, Yan Cheng<sup>1</sup>, Long Chen<sup>2</sup>, Li Yuan<sup>2</sup>, Kevin J. Chen<sup>1</sup>

<sup>1</sup>The Hong Kong University of Science and Technology; <sup>2</sup>Genettice (Qingdao) Semiconductor Material Co. LTD.

**12:00**

**Switching of a Bus Voltage of 1400 V at 10 MHz Using Vertical GaN Fin-JFETs ..... 235**

Andrew Edwards, Vianey Padilla, Cliff Drowley, Subhash Pidaparathi, James Michael, Prashant Saxena, Joseph Tandingan, Wolfgang Meier, Andrew Walker  
*NexGen Power Systems Inc*

**14:00 – 15:40**

**SiC-2: Ruggedness & Reliability of SiC MOSFETs**

**Chairs:** Dethard Peters, *Infineon Technologies*  
Shinsuke Harada, *AIST*

*14:00*

**Improving Surge Current Capability of SBD-Embedded SiC-MOSFETs in Parallel Connection by Applying Bipolar Mode Activation Cells ..... 238**

Akifumi Iijima, Koutarou Kawahara, Katsutoshi Sugawara, Shiro Hino, Katsuhiro Fujiyoshi, Yasunori Oritsuki, Takeshi Murakami, Tetsuo Takahashi, Yasuhiro Kagawa, Yoichi Hironaka, Kazuyasu Nishikawa  
*Mitsubishi Electric Corporation*

*14:25*

**Improvement of Surge Current Capability in SBD-Embedded SiC MOSFETs by Introducing Trigger p-N Diodes ..... 242**

Teruyuki Ohashi<sup>1</sup>, Hiroshi Kono<sup>2</sup>, Shunsuke Asaba<sup>2</sup>, Hideki Hayakawa<sup>2</sup>, Takahiro Ogata<sup>1</sup>, Ryosuke Iijima<sup>1</sup>  
<sup>1</sup>*Toshiba Corporation*; <sup>2</sup>*Toshiba Electronic Devices & Storage Corporation*

*14:50*

**Gate Current Peaks Due to C<sub>GD</sub> Overcharge in SiC MOSFETs Under Short-Circuit Test ..... 246**

Sara Kochoska, Jaume Roig Guitart, Lukas Richert, Basil Vlachakis  
*ON Semiconductor Corporation*

*15:15*

**Investigations of Residual Damage in SiC Trench MOSFETs After Single and Multiple Short-Circuit Stress ..... 250**

Mitsuki Takahashi<sup>1</sup>, Hiroshi Yano<sup>1</sup>, Noriyuki Iwamuro<sup>1</sup>, Shinsuke Harada<sup>2</sup>  
<sup>1</sup>*University of Tsukuba*; <sup>2</sup>*National Institute of Advanced Industrial Science and Technology*

**16:00 – 17:30**

**Poster-2: LVT**

**Chair:** Kuo-Ming Wu, *Taiwan Semiconductor Manufacturing Company*

*Poster Area*

**Isolated JFET Design and Performance Analyze by Experiment Based on Standard 0.18 $\mu$ m BCD Platform ..... 254**

Dingxiang Ma, Yue Gao, Dican Hou, Zhangyi'an Yuan, Ming Qiao, Shaowei Zhen, Bo Zhang  
*University of Electronic Science and Technology of China*

**Mechanism Analysis and Improved Model for HCI in 200V STI-Based Triple RESURF LDMOS with n-p-n Layer ..... 258**

Zuquan Zheng<sup>1</sup>, Ming Qiao<sup>1</sup>, Wenliang Liu<sup>1</sup>, Xingrui Long<sup>1</sup>, Penglong Xu<sup>2</sup>, Chunxia Ma<sup>2</sup>, Feng Lin<sup>2</sup>, Bo Zhang<sup>1</sup>  
<sup>1</sup>*University of Electronic Science and Technology of China*; <sup>2</sup>*CSSMC Technologies Corporation*

**Low Loss Lateral Insulated Gate Bipolar Transistor with an Anode PNP Structure and Integrated Freewheeling Diode ..... 262**

Yuxi Wei<sup>1</sup>, Jie Wei<sup>1</sup>, Pengchen Zhu<sup>1</sup>, Kemeng Yang<sup>2</sup>, Kaiwei Dai<sup>1</sup>, Jie Li<sup>1</sup>, Junnan Wang<sup>1</sup>, Bo Zhang<sup>1</sup>, Xiaorong Luo<sup>1</sup>  
<sup>1</sup>*University of Electronic Science and Technology of China*; <sup>2</sup>*Nanjing University of Posts and Telecommunications*

**0.18 $\mu$ m 200V SOI-BCD Technology with Ultra-Low Specific On-Resistance LDMOS for Automotive Application ..... 266**

Li Lu<sup>1</sup>, Shulang Ma<sup>2</sup>, Jinyu Xiao<sup>2</sup>, Feng Lin<sup>2</sup>, Shuxian Chen<sup>2</sup>, Hong Shao<sup>2</sup>, Sen Zhang<sup>2</sup>, Kui Xiao<sup>2</sup>, Yixin Dai<sup>1</sup>, Zhihan Zhu<sup>1</sup>, Jie Ma<sup>1</sup>, Jiaying Wei<sup>1</sup>, Long Zhang<sup>1</sup>, Siyang Liu<sup>1</sup>, Weifeng Sun<sup>1</sup>  
<sup>1</sup>*National ASIC System Engineering Research Center, Southeast University*; <sup>2</sup>*CSSMC Technologies Corporation*

**Improvement of HCI and HTRB Reliability on 100V pLDMOS for 48V Battery Applications ..... 270**  
Dong-Hoon Park, Min-Woo Kim, Jun-Ki Min, Kwang-Young Ko, Sang-Gi Lee  
*DB HiTek*

**Novel Complementary Lateral IGBTs on Bulk Silicon with Multiple Buried Layers for Perfect Isolation and High Performance ..... 274**  
Zijian Zhang, Xuehao Tang, Kai Chen, Suyang Liu, Masahide Inuishi  
*Waseda University*

**3D Simulation Study of 375V Partial SOI SJ LDNMOS BDS Limitation ..... 278**  
Elizabeth Ching Tee Kho<sup>1</sup>, Marina Antoniou<sup>2</sup>, David Green<sup>3</sup>, Alexander Hölke<sup>4</sup>, Florin Udrea<sup>5</sup>  
<sup>1</sup>*X-FAB Sarawak Sdn. Bhd., Malaysia;* <sup>2</sup>*University of Warwick;* <sup>3</sup>*Silvaco Europe Ltd.;* <sup>4</sup>*X-FAB Global Services GmbH;* <sup>5</sup>*University of Cambridge*

**A Novel Lateral Power MOSFET with Ultra-Low Energy Consumption and Extraordinary Robustness ..... 282**  
Junji Cheng<sup>1,3</sup>, Tao Zhong<sup>1</sup>, Bo Yi<sup>1</sup>, Haimeng Huang<sup>1</sup>, Keqiang Ma<sup>2</sup>, Xinkai Guo<sup>1</sup>, Hongqiang Yang<sup>1</sup>, Zhiming Wang<sup>1</sup>, Guoyi Zhang<sup>3</sup>  
<sup>1</sup>*University of Electronic Science and Technology of China;* <sup>2</sup>*Chengdu Semi-Future Technology Co., Ltd.;* <sup>3</sup>*Peking University*

**16:00 – 17:30**

**Poster-2: PK**

**Chairs:** Alberto Castellazzi, *Kyoto University of Advanced Scienc*

*Poster Area*

**TCAD Simulation Modeling of Mold Epoxy Resin Applied for Encapsulation of Power Devices ..... 286**  
Tomohiro Tamaki<sup>1</sup>, Kohei Ebihara<sup>1</sup>, Kazuya Konishi<sup>1</sup>, Koki Kishimoto<sup>1</sup>, Shinya Soneda<sup>1</sup>, Tetsuo Takahashi<sup>1</sup>, Tetsuya Nitta<sup>1</sup>, Tatsuro Watahiki<sup>1</sup>, Keunsam Lee<sup>2</sup>  
<sup>1</sup>*Mitsubishi Electric Corporation;* <sup>2</sup>*Nihon Synopsys G.K.*

**Simplified Open-Loop Transfer Functions to Analyze Influential Parasitic Parameters for Oscillation Caused by Parallel Connected Transistors ..... 290**  
Hiroto Sakai, Yuta Okawauchi, Shinji Yato, Hideo Araki, Takayuki Atago, Ken Nakahara  
*ROHM Co., Ltd.*

**Lifetime Modeling of SiC MOSFET Power Modules During Power Cycling Tests at Low Temperature Swings ..... 294**  
Felix Hoffmann<sup>1</sup>, Stefan Schmitt<sup>2</sup>, Nando Kaminski<sup>1</sup>  
<sup>1</sup>*University of Bremen;* <sup>2</sup>*SEMIKRON Elektronik GmbH & Co. KG*

**A Symmetric Low-Inductance High-Power Density SiC Power Module for EV Applications ..... 298**  
Haiyong Wan<sup>1</sup>, Marina Antoniou<sup>1</sup>, Nikolaos Iosifidis<sup>1</sup>, Rui Rong<sup>2</sup>, Philip Mawby<sup>1</sup>  
<sup>1</sup>*University of Warwick;* <sup>2</sup>*MacMic Science & Technology Co., Ltd*

**Kirkendall Voids in Soft Soldered Power Packages ..... 302**  
Tim Boettcher<sup>1</sup>, Guerkan Ilicali<sup>1</sup>, Tom Birkoben<sup>1</sup>, Haibo Fan<sup>2</sup>, Max Haenze<sup>1</sup>, Alex Sabelfeld<sup>1</sup>, Soenke Kahl<sup>1</sup>  
<sup>1</sup>*Nexperia Germany GmbH;* <sup>2</sup>*Nexperia Hong Kong*

**Coupled Structural and Functional Characterization and Modelling of Integrated GaN Half-Bridge Power Switches ..... 306**  
Ciro Scognamiglio<sup>1</sup>, Antonio Pio Catalano<sup>1</sup>, Enzo d' Alessandro<sup>1</sup>, Hamzeh J. Jaber<sup>2</sup>, Alberto Castellazzi<sup>2</sup>  
<sup>1</sup>*Università degli Studi di Napoli Federico II;* <sup>2</sup>*Kyoto University of Advanced Science*

|                                                                                                                                                                                                                                                                   |            |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------|
| <b>In-Situ Extraction of the Thermal Impedance of GaN Power HEMTs Embedded in PCB-Based Power Circuits</b> .....                                                                                                                                                  | <b>310</b> |
| A.P. Catalano <sup>1</sup> , C. Scognamillo <sup>1</sup> , V. d'Alessandro <sup>1</sup> , L. Codecasa <sup>2</sup>                                                                                                                                                |            |
| <sup>1</sup> Università degli Studi di Napoli Federico II; <sup>2</sup> Politecnico di Milano                                                                                                                                                                     |            |
| <br><b>16:00 – 17:30</b>                                                                                                                                                                                                                                          |            |
| <b>Poster-2: SiC</b>                                                                                                                                                                                                                                              |            |
| <b>Chairs:</b> Chih-Fang Huang, <i>National Tsing Hua University</i>                                                                                                                                                                                              |            |
| <i>Poster Area</i>                                                                                                                                                                                                                                                |            |
| <b>Impact of Layout Arrangement on Surge Current and Avalanche Robustness of Silicon Carbide JBS Diodes</b> .....                                                                                                                                                 | <b>314</b> |
| Fu-Jen Hsu <sup>1,2</sup> , Hsiang-Ting Hung <sup>2</sup> , Cheng-Tyng Yen <sup>2</sup>                                                                                                                                                                           |            |
| <sup>1</sup> National Tsing Hua University; <sup>2</sup> Fast SiC Semiconductor Inc.                                                                                                                                                                              |            |
| <br><b>Mechanism of Threshold Voltage Instability in SiC MOSFETs and Impacts on Dynamic Switching</b> .....                                                                                                                                                       | <b>318</b> |
| Junsong Jiang <sup>1</sup> , Mohan Tian <sup>1</sup> , Wen Ji <sup>1,2</sup> , Zhihao Hu <sup>1</sup> , Haoran Li <sup>1</sup> , Yuzheng Guo <sup>2</sup> , Zhaofu Zhang <sup>2</sup> , Xi Tang <sup>1</sup> , Cungang Hu <sup>1</sup> , Wenping Cao <sup>1</sup> |            |
| <sup>1</sup> Anhui University; <sup>2</sup> Wuhan University                                                                                                                                                                                                      |            |
| <br><b>The Impact of the Dead-Time on the Reverse Recovery Behavior of SiC-MOSFET Body Diodes</b> .....                                                                                                                                                           | <b>322</b> |
| Xing Liu, Xupeng Li, Clemens Herrmann, Thomas Basler                                                                                                                                                                                                              |            |
| <i>Chemnitz University of Technology</i>                                                                                                                                                                                                                          |            |
| <br><b>5 A/1.17 kV NiO/<math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> Heterojunction Power Rectifier with High-Temperature Operation Capability Up to 548 K</b> .....                                                                                             | <b>326</b> |
| Zhengpeng Wang, Hehe Gong, Xinxin Yu, Fangfang Ren, Shulin Gu, Youdou Zheng, Rong Zhang, Jiandong Ye                                                                                                                                                              |            |
| <i>Nanjing University</i>                                                                                                                                                                                                                                         |            |
| <br><b>An Electro-Thermal Co-Designed Ga<sub>2</sub>O<sub>3</sub> [100] Trench Power Diode Featuring Ferroelectric Dielectric</b> .....                                                                                                                           | <b>330</b> |
| Yuan Li, Yitong Yang, Xiaoli Lu, Yunlong He, Xiaohua Ma, Yue Hao                                                                                                                                                                                                  |            |
| <i>Xidian University</i>                                                                                                                                                                                                                                          |            |
| <br><b>1.2 kV SiC MOSFET Body Diode Turn-Off in Fast Switching: Channel Conduction, Carrier Plasma and Parasitic Turn-On</b> .....                                                                                                                                | <b>334</b> |
| Thanh-Toan Pham, Jimmy Franchi, Kwangwon Lee, Martin Domeij                                                                                                                                                                                                       |            |
| <i>ON Semiconductor Corporation</i>                                                                                                                                                                                                                               |            |
| <br><b>Stability Analysis of Parallel SiC Power MOSFETs Based on a Virtual Prototype</b> .....                                                                                                                                                                    | <b>338</b> |
| Michel Nagel <sup>1</sup> , Ivana Kovacevic-Badstuebner <sup>1</sup> , Race Salvatore <sup>1</sup> , Dan Popescu <sup>2</sup> , Bogdan Popescu <sup>2</sup> , Daniele Romano <sup>3</sup> , Giulio Antonini <sup>3</sup> , Ulrike Grossner <sup>1</sup>           |            |
| <sup>1</sup> APS Laboratory, ETH Zürich; <sup>2</sup> Infineon Technologies AG; <sup>3</sup> University of L'Aquila                                                                                                                                               |            |
| <br><b>Fabrication of Ampere-Class p-Cu<sub>2</sub>O/n-<math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> Trench Heterojunction Barrier Schottky Diodes and Double-Pulse Evaluation</b> .....                                                                         | <b>342</b> |
| Akio Takatsuka, Hironobu Miyamoto, Kohei Sasaki, Akito Kuramata                                                                                                                                                                                                   |            |
| <i>Novel Crystal Technology, Inc.</i>                                                                                                                                                                                                                             |            |
| <br><b>Self-Clamped P-Shield SiC Trench IGBT for Low On-State Voltage and Switching Loss</b> .....                                                                                                                                                                | <b>346</b> |
| Xuan Li, Qian Lou, Hanqing Zhao, Xiaochuan Deng, Bo Zhang                                                                                                                                                                                                         |            |
| <i>University of Electronic Science and Technology of China</i>                                                                                                                                                                                                   |            |

|                                                                                                                                                                                                                                                                                                                                                                                                                                                                    |            |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------|
| <b>Improved Blocking and Switching Characteristics of Split-Gate 1.2kV 4H-SiC MOSFET with a Deep P-Well .....</b>                                                                                                                                                                                                                                                                                                                                                  | <b>350</b> |
| Dongyoung Kim, Skylar Deboer, Seung Yup Jang, Adam J. Morgan, Woongje Sung<br><i>State University of New York Polytechnic Institute</i>                                                                                                                                                                                                                                                                                                                            |            |
| <b>Short-Circuit Rugged 1.2 kV SiC MOSFET with a Non-Linear Dielectric Gate Stack .....</b>                                                                                                                                                                                                                                                                                                                                                                        | <b>354</b> |
| M. Boccarossa <sup>1</sup> , L. Maresca <sup>1</sup> , A. Borghese <sup>1</sup> , M. Riccio <sup>1</sup> , G. Breglio <sup>1</sup> , A. Irace <sup>1</sup> , G.A. Salvatore <sup>2</sup><br><sup>1</sup> <i>Università degli Studi di Napoli Federico II</i> ; <sup>2</sup> <i>Università Ca' Foscari Venezia</i>                                                                                                                                                  |            |
| <b>Enhanced Design Architecture to Suppress Leakage Current of High-Voltage (HV) Lateral nMOSFETs in 4H-SiC .....</b>                                                                                                                                                                                                                                                                                                                                              | <b>358</b> |
| Sundar Babu Isukapati, Seung Yup Jang, Woongje Sung<br><i>State University of New York Polytechnic Institute</i>                                                                                                                                                                                                                                                                                                                                                   |            |
| <b>Experimental Demonstration of dV/dt Effect on Silicon Carbon SGTO for Pulse Power Applications .....</b>                                                                                                                                                                                                                                                                                                                                                        | <b>362</b> |
| Chao Liu <sup>1</sup> , Ziwen Chen <sup>1</sup> , Qingyu Liu <sup>1</sup> , Ruize Sun <sup>1</sup> , Wanjun Chen <sup>1</sup> , Zhaoji Li <sup>1</sup> , Bo Zhang <sup>1</sup> , Heng Deng <sup>2</sup> , Yijun Shi <sup>3</sup><br><sup>1</sup> <i>University of Electronic Science and Technology of China</i> ; <sup>2</sup> <i>Xi'an Modern Control Technology Research Institute</i> ;<br><sup>3</sup> <i>The Fifth Electronic Research Institute of MIIT</i> |            |
| <b>Electrical Characterization and Analysis of 4H-SiC Lateral MOSFET (LMOS) for High-Voltage Power Integrated Circuits .....</b>                                                                                                                                                                                                                                                                                                                                   | <b>366</b> |
| Li Liu <sup>1</sup> , Jue Wang <sup>2</sup> , Zishi Wang <sup>1</sup> , Miaoguang Bai <sup>1</sup> , Junze Li <sup>1</sup> , Zhengyun Zhu <sup>1</sup> , Hongyi Xu <sup>3</sup> , Na Ren <sup>1</sup> , Qing Guo <sup>1</sup> , Kuang Sheng <sup>1</sup><br><sup>1</sup> <i>Zhejiang University</i> ; <sup>2</sup> <i>Hangzhou City University</i> ; <sup>3</sup> <i>ZJU-Hangzhou Global Scientific and Technological Innovation Center</i>                        |            |

## Thursday, June 1, 2023

8:45 – 10:25

### GaN-3: Novel GaN Power Devices & Technologies 2

**Chairs:** Hong Zhou, *Xidian University*  
Hideyuki Okita, *Panasonic*

8:45

#### **3.0-V-Threshold-Voltage p-GaN HEMTs with Low-Loss Reverse Conduction Capability .....**

Feng Zhou<sup>1</sup>, Weizong Xu<sup>1</sup>, Yulei Jin<sup>1</sup>, Tianyang Zhou<sup>1</sup>, Fangfang Ren<sup>1</sup>, Dong Zhou<sup>1</sup>, Yuanyang Xia<sup>2</sup>, Leke Wu<sup>2</sup>, Yiheng Li<sup>2</sup>, Tinggang Zhu<sup>2</sup>, Dunjun Chen<sup>1</sup>, Rong Zhang<sup>1</sup>, Youdou Zheng<sup>1</sup>, Hai Lu<sup>1</sup>  
<sup>1</sup>*Nanjing University*; <sup>2</sup>*CorEnergy Semiconductor Co. Ltd.*

9:10

#### **10 A/950 V Switching of GaN-Channel HFETs with Non-Doped AlN Buffer .....**

Oliver Hilt, Frank Brunner, Mihaela Wolf, Eldad Bahat Treidel, Joachim Würfl, Andreas Thies, Anna Mogilatenko  
*Ferdinand-Braun-Institut gGmbH*

9:35

#### **High Dynamic Stability in Enhancement-Mode Active-Passivation p-GaN Gate HEMT .....**

Yanlin Wu<sup>1</sup>, Muqin Nuo<sup>1</sup>, Junjie Yang<sup>1</sup>, Zheyang Zheng<sup>2</sup>, Li Zhang<sup>2</sup>, Kevin J. Chen<sup>2</sup>, Mengyuan Hua<sup>3</sup>, Yilong Hao<sup>1</sup>, Xuelin Yang<sup>1</sup>, Bo Shen<sup>1</sup>, Maojun Wang<sup>1</sup>, Jin Wei<sup>1</sup>  
<sup>1</sup>*Peking University*; <sup>2</sup>*The Hong Kong University of Science and Technology*; <sup>3</sup>*Southern University of Science and Technology*

10:00

**Impact of Gate Morphology on Electrical Performances of Recessed GaN-On Si MOS Channel-HEMT for Different Channel Orientations ..... 382**

C. Piotrowicz<sup>1,2</sup>, B. Mohamad<sup>1</sup>, P. Fernandes Paes Pinto Rocha<sup>2</sup>, N. Malbert<sup>2</sup>, S. Ruel<sup>1</sup>, P. Pimenta-Barros<sup>1</sup>, M.-A. Jaud<sup>1</sup>, L. Vauche<sup>1</sup>, C. Le Royer<sup>1</sup>

<sup>1</sup>CEA-Leti; <sup>2</sup>UMR 5218 - IMS - Laboratoire de l'Intégration du Matériau au Système

10:45 – 12:00

**SiC-3: Recent Advances in Ga<sub>2</sub>O<sub>3</sub> Devices**

**Chairs:** Cheng-Tyng Yen, *Fast SiC Semiconductor Inc.*

Alexander Bolotnikov, *ON Semiconductor*

10:45

**NiO Junction Termination Extension for Ga<sub>2</sub>O<sub>3</sub> Devices: High Blocking Field, Low Capacitance, and Fast Switching Speed ..... 386**

Ming Xiao<sup>1</sup>, Boyan Wang<sup>1</sup>, Ruizhe Zhang<sup>1</sup>, Qihao Song<sup>1</sup>, Joseph Spencer<sup>1,2</sup>, Zhonghao Du<sup>3</sup>, Yuan Qin<sup>1</sup>, Kohei Sasaki<sup>4</sup>, Han Wang<sup>3</sup>, Marko Tadjer<sup>2</sup>, Yuhao Zhang<sup>1</sup>

<sup>1</sup>Virginia Polytechnic Institute and State University; <sup>2</sup>U.S. Naval Research Laboratory;

<sup>3</sup>University of Southern California; <sup>4</sup>Novel Crystal Technology, Inc.

11:10

**An E-Mode  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> Metal-Heterojunction Composite Field Effect Transistor with a Record High P-FOM of 0.73 GW/cm<sup>2</sup> ..... 390**

Xichen Wang, Xiaoli Lu, Yunlong He, Peng Liu, Yv Shao, Jianing Li, Yitong Yang, Yuan Li, Yue Hao, Xiaohua Ma  
*Xidian University*

11:35

**1 kV Vertical  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> Heterojunction Barrier Schottky Diode with Hybrid Unipolar and Bipolar Operation ..... 394**

Weibing Hao, Qiming He, Zhao Han, Xiaolong Zhao, Guangwei Xu, Shu Yang, Shibing Long  
*University of Science and Technology of China*

13:45 – 15:00

**LVT-2: Lateral Low Voltage Devices**

**Chairs:** Xin Lin, *NXP Semiconductors*

Riccardo Depetro, *STMicroelectronics*

13:45

**Compact 200V Diode Constructed on Thick SOI Wafer ..... 398**

Jaroslav Pjencak, Ladislav Seliga  
*ON Semiconductor Corporation, Czechia*

14:10

**A 600V HVIC with Integrated Bootstrap Diode Function by a New Emulating HV MOS ..... 402**

Yuji Kawasaki<sup>1</sup>, Toshihiro Imasaka<sup>1</sup>, Yuto Shibuta<sup>2</sup>, Shohei Sano<sup>2</sup>, Yo Habu<sup>1</sup>, Nobuo Hashimoto<sup>2</sup>, Mitsutaka Hano<sup>1</sup>, Manabu Yoshino<sup>1</sup>

<sup>1</sup>Mitsubishi Electric Corporation; <sup>2</sup>Melco Semiconductor Engineering Corporation

14:35

**Experimental Study on SOI LIGBT with Field Plate Resistances at Anode Side ..... 406**

Jie Wei<sup>1</sup>, Pengchen Zhu<sup>1</sup>, Yuxi Wei<sup>1</sup>, Kemeng Yang<sup>3</sup>, Jie Li<sup>1</sup>, Junnan Wang<sup>1</sup>, Kaiwei Dai<sup>1</sup>, Hua Song<sup>2</sup>, Sen Zhang<sup>2</sup>, Wentong Zhang<sup>1</sup>, Bo Zhang<sup>1</sup>, Xiaorong Luo<sup>1</sup>

<sup>1</sup>University of Electronic Science and Technology of China; <sup>2</sup>CSMC Technologies Corporation;

<sup>3</sup>Nanjing University of Posts and Telecommunications